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INTERNATIONAL

SOD-323



SDB720WS

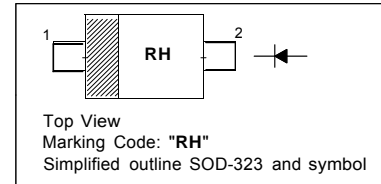
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SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for high frequency rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

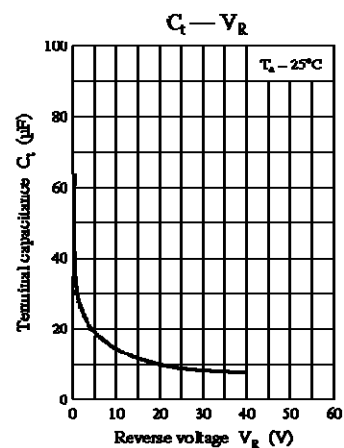
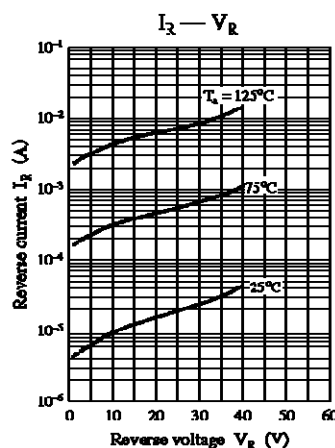
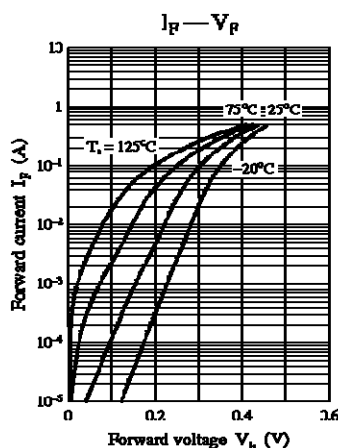


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Forward Current	I_O	0.5	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	2	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 500\text{ mA}$	V_F	-	0.55	V
Reverse Current at $V_R = 35\text{ V}$	I_R	-	100	μA
Terminal Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	60	-	pF
Reverse Recovery Time at $I_F = I_R = 100\text{ mA}$, $I_{rr} = 10\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	5	-	nS





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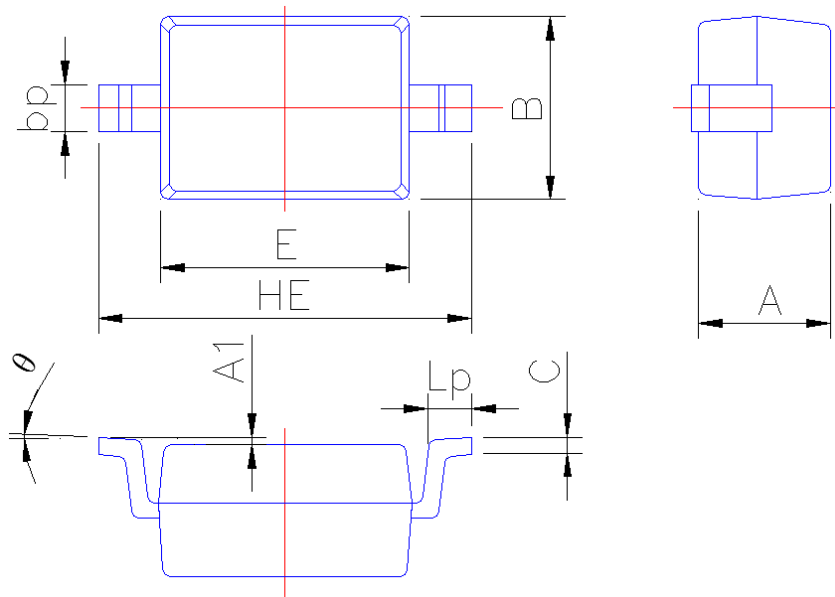


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°